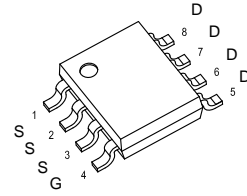




Product Summary

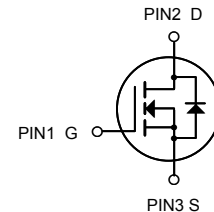
V_{DS}	60V
I_D (at $V_{GS}=10V$)	13.5A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 9.8m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 13.5m Ω



SOP08

General Description

- Trench Power AlphaSGT™ technology
- Low $R_{DS(ON)}$
- Low Gate Charge



N-Channel MOSFET

Applications

- High efficiency power supply
- Secondary synchronous rectifier

Orderable Part Number	Package Type	Form	Minimum Order Quantity	
4264E	SOP08	Tape & Reel	3000	
Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter	Symbol	Maximum	Units	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	13.5	
		$T_A=70^\circ\text{C}$	10.5	
Pulsed Drain Current ^C	I_{DM}	54	A	
Avalanche Current ^C	I_{AS}	17	A	
Avalanche energy $L=0.3\text{mH}$ ^C	E_{AS}	43	mJ	
V_{DS} Spike ^G	V_{SPIKE}	72	V	
Power Dissipation ^B	P_D	$T_A=25^\circ\text{C}$	3.1	
		$T_A=70^\circ\text{C}$	2.0	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Thermal Characteristics				
Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10\text{s}$	31	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D}		Steady-State	59	$^\circ\text{C/W}$
Maximum Junction-to-Lead	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.4	1.8	2.4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =13.5A T _J =125°C		8 12.5	9.8 15.0	mΩ
		V _{GS} =4.5V, I _D =11.5A		10.5	13.5	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =13.5A		48		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.72	1	V
I _S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, f=1MHz		1100		pF
C _{OSS}	Output Capacitance			300		pF
C _{ISS}	Reverse Transfer Capacitance			28		pF
R _g	Gate resistance	f=1MHz	0.6	1.2	2.0	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =13.5A		14.5	25	nC
Q _{g(4.5V)}	Total Gate Charge			7	13	nC
Q _{gs}	Gate Source Charge			2.5		nC
Q _{gd}	Gate Drain Charge			3.5		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =30V, R _L =2.2Ω, R _{GEN} =3Ω		6.5		ns
t _r	Turn-On Rise Time			3.5		ns
t _{D(off)}	Turn-Off DelayTime			22		ns
t _f	Turn-Off Fall Time			3		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =13.5A, di/dt=500A/μs		18.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =13.5A, di/dt=500A/μs		59		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The spike duty cycle 5% max, limited by junction temperature T_{J(MAX)}=125° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

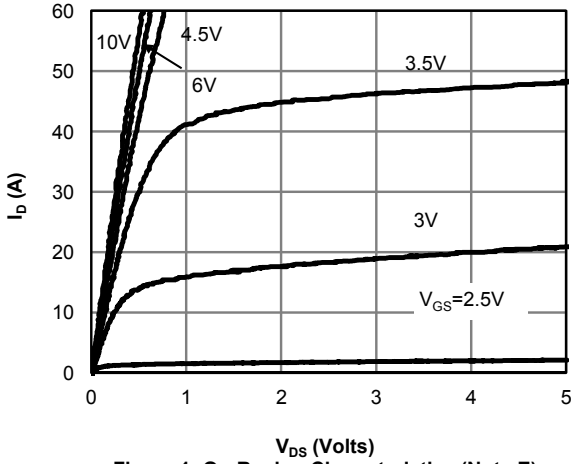


Figure 1: On-Region Characteristics (Note E)

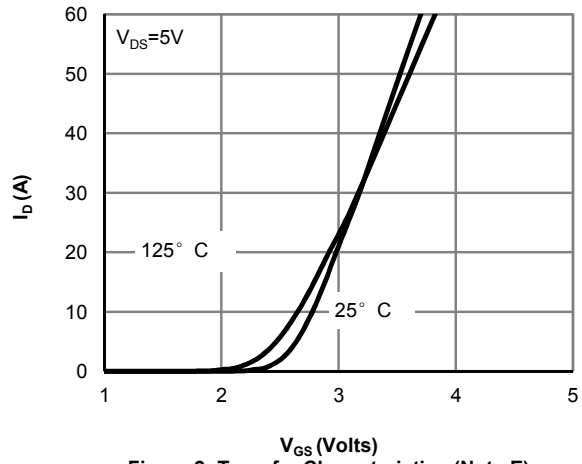


Figure 2: Transfer Characteristics (Note E)

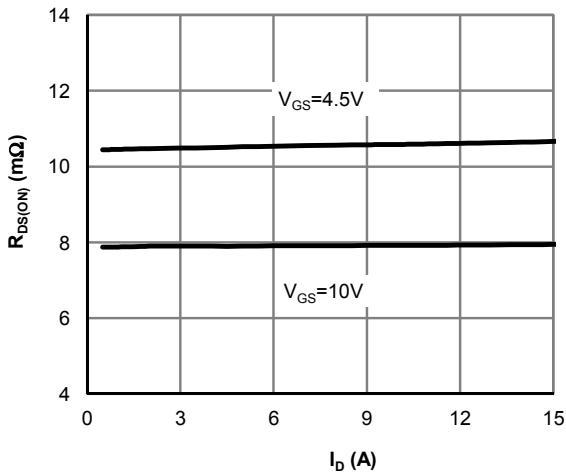


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

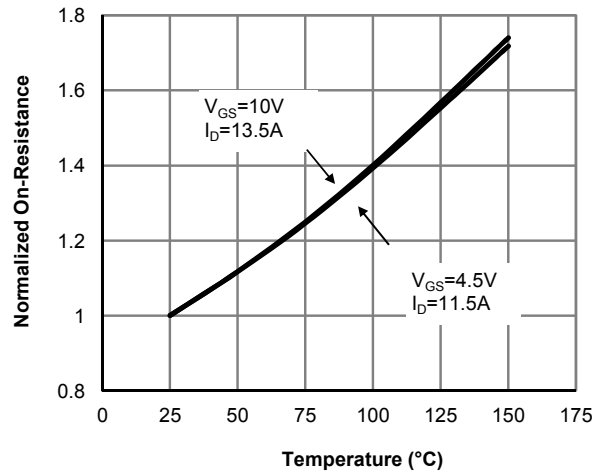


Figure 4: On-Resistance vs. Junction Temperature (Note E)

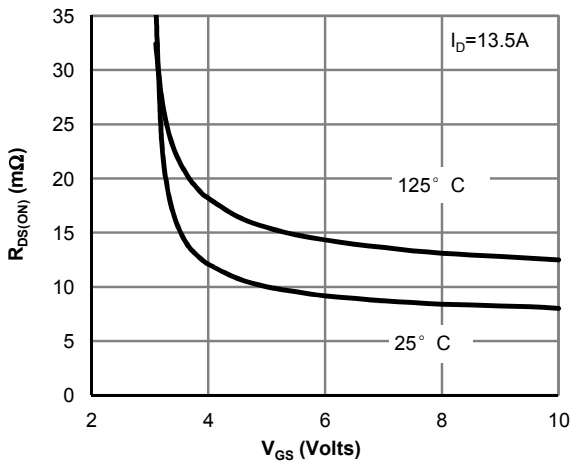


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

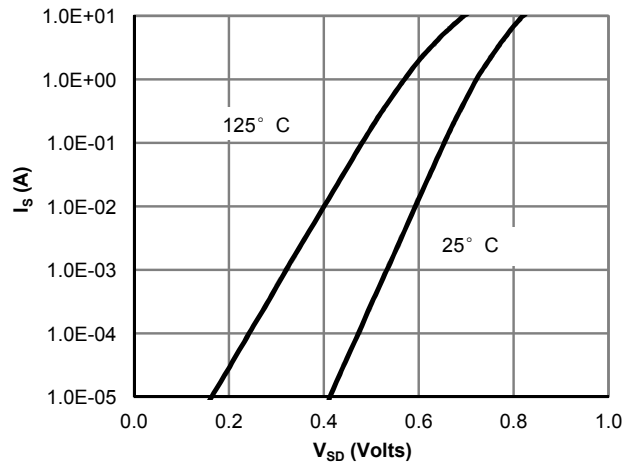


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

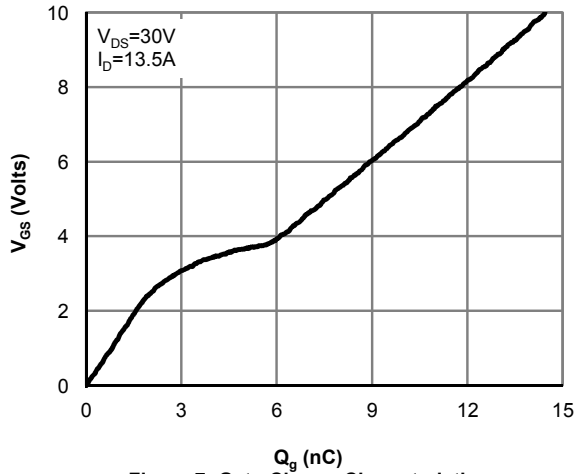


Figure 7: Gate-Charge Characteristics

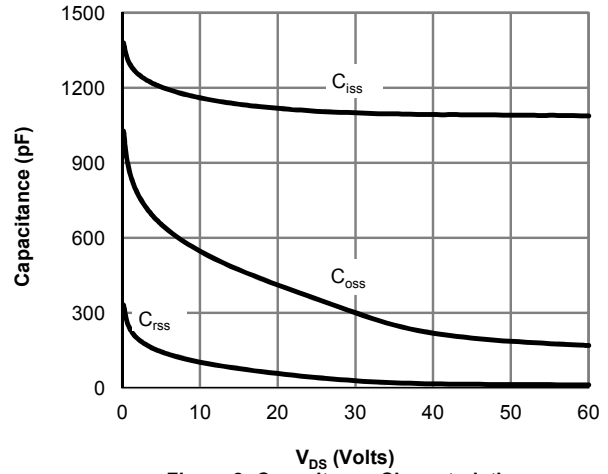


Figure 8: Capacitance Characteristics

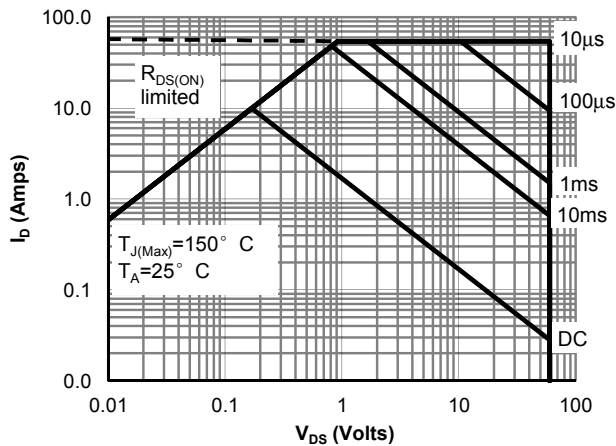


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

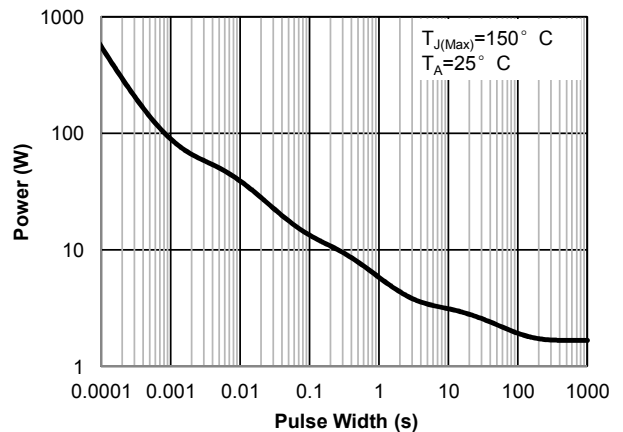


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

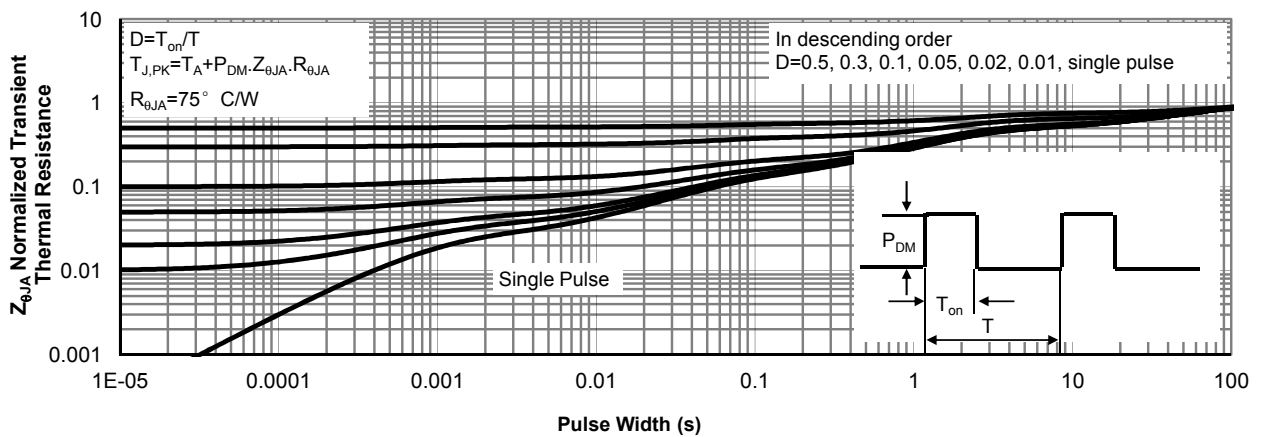


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Figure A: Gate Charge Test Circuit & Waveforms

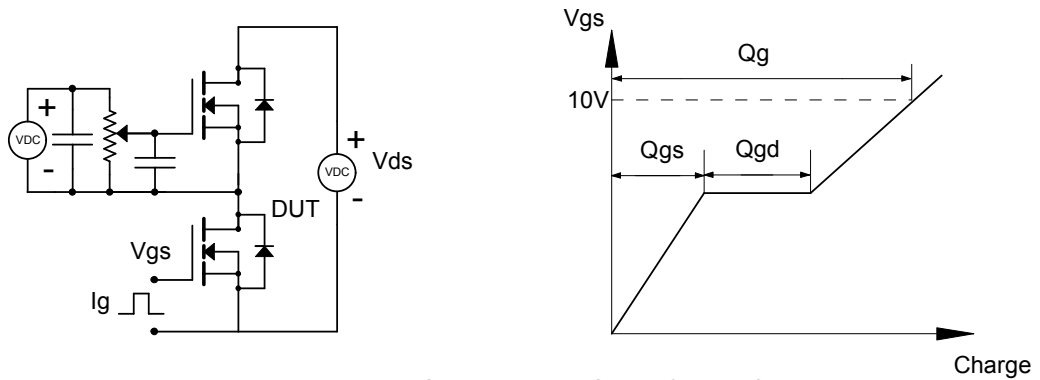


Figure B: Resistive Switching Test Circuit & Waveforms

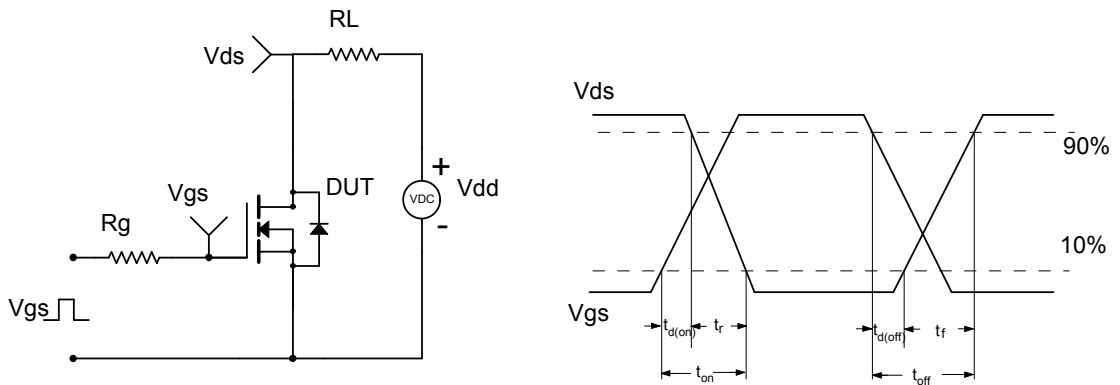


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

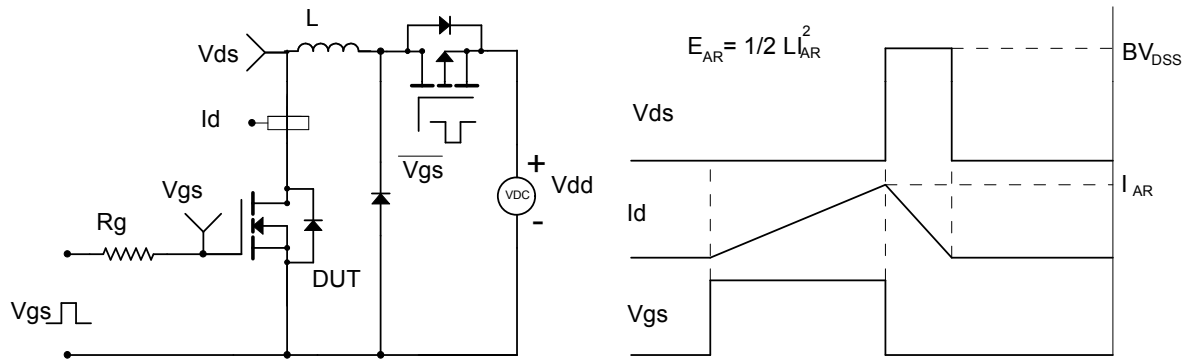
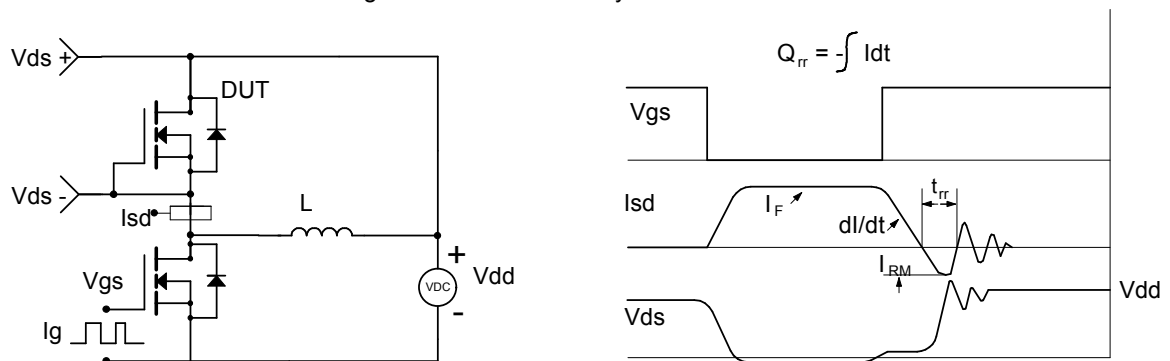
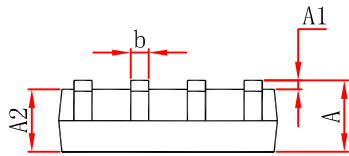
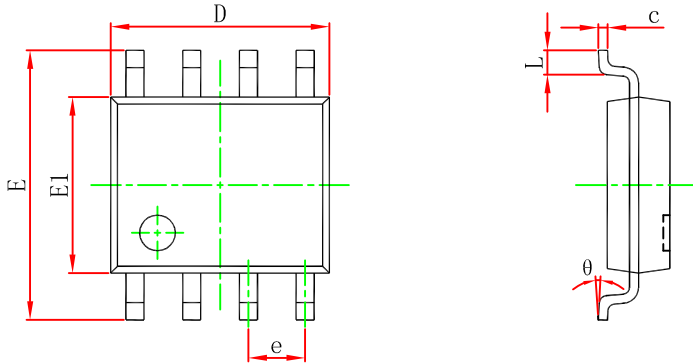


Figure D: Diode Recovery Test Circuit & Waveforms

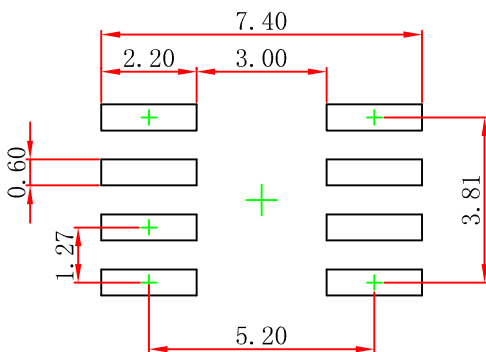




Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A				
A1				
A2				
b				
c				
D				
e	Ä % 6 & Ä		Ä % 6 & Ä	
E				
E1				
L				
	©	e	e	e

e

6P8 6XJJHVWHG 3DG /D\RXW



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.